Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used where "high junction operating temperature" capability ( $T_i = 150$  °C) is required.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

# 3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls for home appliances
- Refrigeration and air-conditioner compressor controls

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	-	60	Α
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 114$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	6	Α





Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static charac	teristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$		-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA
Dynamic cha	racteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit		50	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 ^{\circ}\text{C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 1 \text{ V}/\mu\text{s}; gate open circuit}$		5	-	-	A/ms

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		Symbol 1
mb	n.c.	mounting base; isolated		
			U U U 1 2 3	
			TO-220F (SOT186A)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
BTA206X-800ET	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A					

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 114 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	6	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	60	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	66	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	18	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 10 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

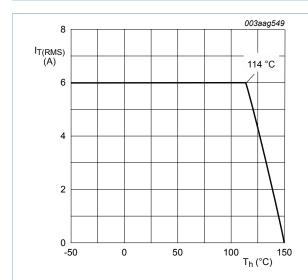
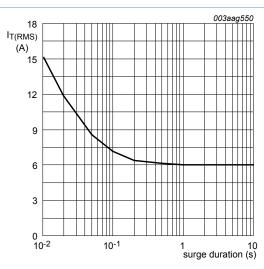


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 114 ^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

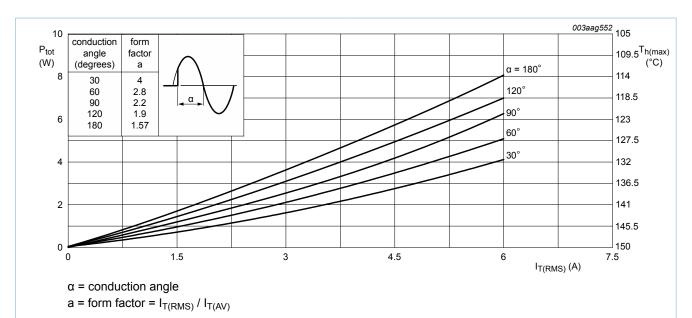


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

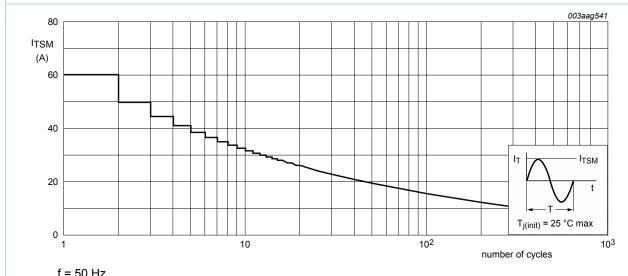
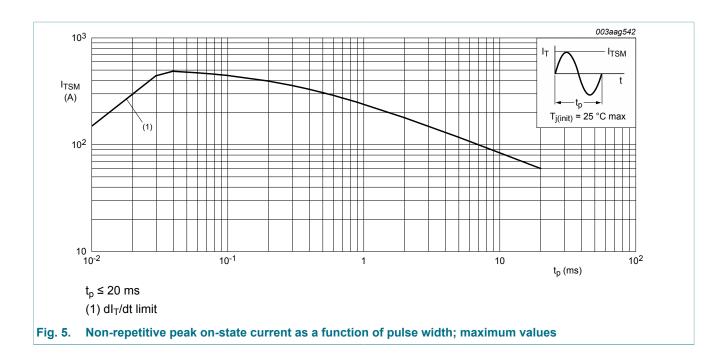


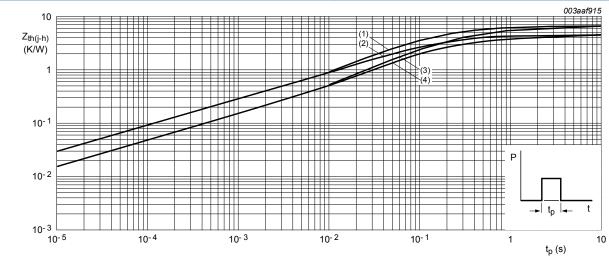
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4.5	K/W
heatsink	heatsink	full cycle or half cycle; without heatsink compound; Fig. 6	-	-	6.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

### 9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

BTA206X-800ET

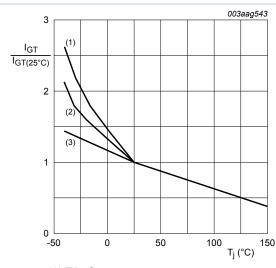
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# 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 7 A; <u>Fig. 10</u>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 150 °C	0.25	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.4	2	mA
Dynamic cl	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	50	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 6 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	1	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 6 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	2	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 6 A; $dV_{com}/dt$ = 1 V/ $\mu$ s; gate open circuit	5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

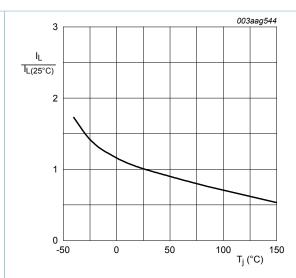


Fig. 8. Normalized latching current as a function of junction temperature

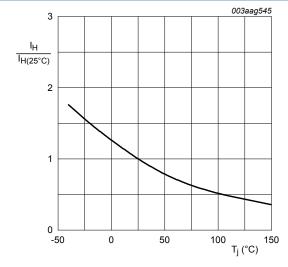
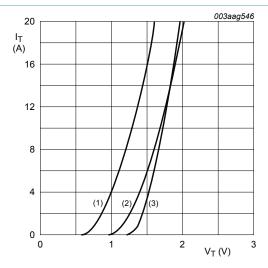


Fig. 9. Normalized holding current as a function of junction temperature



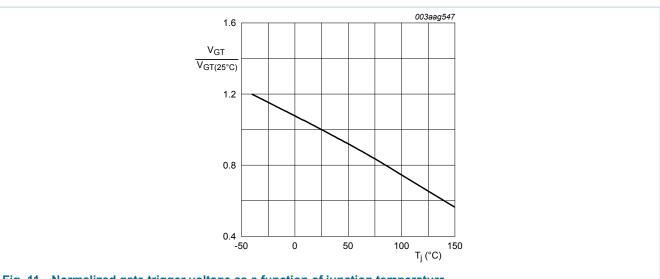
 $V_0 = 1.184 \text{ V}; R_s = 0.047 \Omega$ 

(1) T<sub>j</sub> = 150 °C; typical values

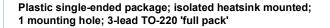
(2) T<sub>i</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

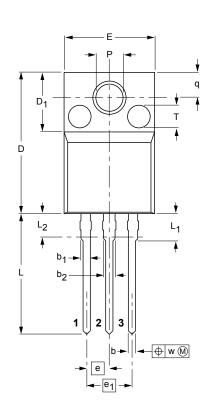
Fig. 10. On-state current as a function of on-state voltage

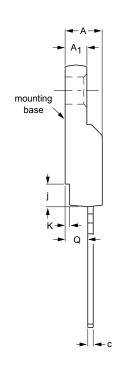


# 11. Package outline



SOT186A





0 5 10 mm

#### **DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	С	D	D <sub>1</sub>	E	е	e <sub>1</sub>	j	к	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	Р	Q	q	T <sup>(2)</sup>	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are #  $2.5 \times 0.8$  max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F				<del>-02-04-09</del> 06-02-14

Fig. 12. Package outline TO-220F (SOT186A)

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